

Attorney Docket No.: 5308-389

IFW
PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re: Saxler
Application No.: 10/772,882
Filed: February 5, 2004

Confirmation No.: 8522
Group Art Unit: 2815
Examiner Name: Jerome Jackson, Jr.

For: **NITRIDE HETEROJUNCTION TRANSISTORS HAVING CHARGE-TRANSFER
INDUCED ENERGY BARRIERS AND METHODS OF FABRICATING THE
SAME**

Date: June 14, 2005

Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. § 1.97(b)

Sir:

Attached is a list of documents on Form PTO-1449, together with a copy of any listed foreign patent document and/or non-patent literature. A copy of any listed U.S. patent and/or U.S. patent application publication is not provided herewith in accordance with the amendment by the U.S. Patent and Trademark Office to 37 C.F.R. § 1.98(a)(2)(ii) effective October 21, 2004. Also enclosed is a translation or a concise explanation of each non-English language document enclosed. It is requested that these documents be considered by the Examiner and officially made of record in accordance with the provisions of 37 C.F.R. § 1.56 and Section 609 of the MPEP.

This Information Disclosure Statement is submitted in accordance with 37 C.F.R. § 1.97(b), within three months of the filing date of the above-referenced application or before the mailing of a first Office Action on the merits, whichever event occurs last. Therefore, no fee is believed due. However, the Commissioner is hereby authorized to charge any deficiency or credit any overpayment to Deposit Account No. 50-0220.

Respectfully submitted,

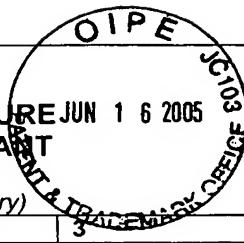
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CERTIFICATE OF MAILING UNDER 37 CFR 1.8

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to: Mail Stop Amendment, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on June 14, 2005.

Erin A. Campion



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STATEMENT BY APPLICANT**

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Application Number 10/772,882

Filing Date February 5, 2004

First Named Inventor

Group Art Unit 281

Examiner Name Jerome Jackson, Jr.

Attorney Docket Number 5308-389

U.S. PATENTS AND PATENT PUBLICATIONS

FOREIGN PATENT DOCUMENTS

OTHER NON PATENT LITERATURE DOCUMENTS

| Examiner Initials* | Cite No. | Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published | T |
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Examiner Signature _____ Date Considered _____

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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| Examiner Name | Jerome Jackson, Jr. |

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| | 26. | United States Patent Application entitled "Methods of Fabricating Nitride-Based Transistors with a Cap Layer and a Recessed Gate," Serial No. 10/897,726, filed July 23, 2004 (Attorney Docket No. 5308-392). | |
| | 27. | United States Patent Application entitled "High Power Density and/or Linearity Transistors," Serial No. 11/005,107, filed December 6, 2004 (Attorney Docket No. 5308-511). | |
| | 28. | United States Patent Application entitled "Field Effect Transistors (FETs) Having Multi-Watt Output Power at Millimeter-Wave Frequencies," Serial No. 11/005,423, filed December 6, 2004 (Attorney Docket No. 5308-512). | |
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| | 30. | United States Patent Application entitled "Aluminum Free Group III-Nitride Based High Electron Mobility Transistors and Methods of Fabricating Same," Serial No. 11/118,575, filed April 29, 2005 (Attorney Docket No. 5308-543). | |
| | 31. | United States Patent Application entitled "Binary Group III-Nitride Based High Electron Mobility Transistors and Methods of Fabricating Same," Serial No. 11/118,675, filed April 29, 2005 (Attorney Docket No. 5308-544). | |
| | 32. | United States Patent Application entitled "Composite Substrates of Conductive And Insulating or Semi-Insulating Group III-Nitrides For Group III-Nitride Devices," Serial No. 11/103,127, filed April 11, 2005 (Attorney Docket No. 5308-551). | |
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Examiner Signature

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